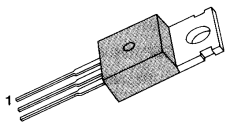
# BD244/A/B/C PNP EPITAXIAL SILICON TRANSISTOR

## MEDIUM POWER LINEAR AND SWITCHING APPLICATIONS

- Complement to BD243, BD243A, BD243B and BD243C respectively

TO-220




1.Base 2.Collector 3.Emitter

## ABSOLUTE MAXIMUM RATINGS

| Characteristic | Symbol | Rating | Unit |
|---|---|---|---|
| Collector-Emitter Voltage : BD244 | $V_{CBO}$ | - 45 | V |
| : BD244A | | - 60 | V |
| : BD244B | | - 80 | V |
| : BD244C | | - 100 | V |
| Collector Emitter Voltage : BD244 | $V_{CEO}$ | - 45 | V |
| : BD244A | | - 60 | V |
| : BD244B | | - 80 | V |
| : BD244C | | - 100 | V |
| Emitter Base Voltage | $V_{EBO}$ | - 5 | V |
| Collector Current (DC) | $I_C$ | - 6 | A |
| Collector Current (Pulse) | $I_C$ | - 10 | A |
| Base Current | $I_B$ | - 2 | A |
| Collector Dissipation ($T_C$=25°C) | $P_C$ | 65 | W |
| Junction Temperature | $T_J$ | 150 | °C |
| Storage Temperature | $T_{STG}$ | -65 ~ 150 | °C |

## ELECTRICAL CHARACTERISTICS ($T_C$=25°C)

| Characteristic | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| * Collector Emitter Sustaining Voltage : BD244 | $V_{CEO}$(sus) | $I_C$ = - 30mA, $I_B$ = 0 | - 45 | | | V |
| : BD244A | | | - 60 | | | V |
| : BD244B | | | - 80 | | | V |
| : BD244C | | | - 100 | | | V |
| Collector Cutoff Current : BD244/244A | $I_{CEO}$ | $V_{CE}$ = - 30V, $I_B$ = 0 | | | - 0.7 | mA |
| : BD244B/244C | | $V_{CE}$ = - 60V, $I_B$ = 0 | | | - 0.7 | mA |
| Collector Cutoff Current : BD244 | $I_{CES}$ | $V_{CE}$ = - 45V, $V_{BE}$ = 0 | | | - 0.4 | mA |
| : BD244A | | $V_{CE}$ = - 60V, $V_{BE}$ = 0 | | | - 0.4 | mA |
| : BD244B | | $V_{CE}$ = - 80V, $V_{BE}$ = 0 | | | - 0.4 | mA |
| : BD244C | | $V_{CE}$ = - 100V, $V_{BE}$ = 0 | | | - 0.4 | mA |
| Emitter Cutoff Current | $I_{EBO}$ | $V_{EB}$ = - 5V, $I_C$ = 0 | | | - 1 | mA |
| * DC Current Gain | $h_{FE}$ | $V_{CE}$ = - 4V, $I_C$ = - 0.3A | 30 | | | |
| | | $V_{CE}$ = - 4V, $I_C$ = - 3A | 15 | | | |
| * Collector Emitter Saturation Voltage | $V_{CE}$(sat) | $I_C$ = - 6A, $I_B$ = - 1A | | | - 1.5 | V |
| * Base Emitter On Voltage | $V_{BE}$(on) | $V_{CE}$ = - 4V, $I_C$ = - 6A | | | - 2 | V |

* Pulse Test: PW=300μs, duty Cycle<2% Pulsed



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